

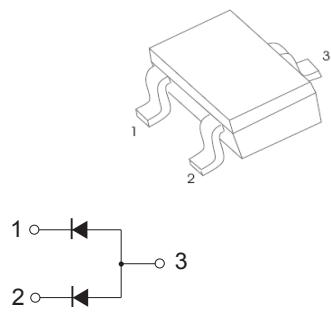
## Plastic-Encapsulate Transistors

### **DAP222T** SWITCHING DIODE

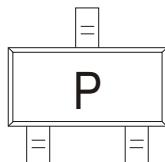
#### FEATURES:

- High speed
- Suitable for high packing density layout
- High reliability

**SOT-523**



**MARKING: P**



#### Maximum Ratings @Ta=25°C

Parameter	Symbol	Limit	Unit
Non-Repetitive Peak Reverse Voltage	V <sub>RM</sub>	80	V
DC Blocking Voltage	V <sub>R</sub>	80	V
Forward Continuous Current	I <sub>FM</sub>	300	mA
Non-Repetitive Peak Forward Surge Current @t=8.3ms	I <sub>FSM</sub>	2.0	A
Average Rectified Output Current	I <sub>O</sub>	100	mA
Power Dissipation	P <sub>D</sub>	150	mW
Thermal resistance From Junction to ambient	R <sub>θJA</sub>	833	°C/W
Operation Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55~+150	°C

#### ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	V <sub>(BR)</sub>	I <sub>R</sub> = 100μA	80		V
Reverse voltage leakage current	I <sub>R</sub>	V <sub>R</sub> =70V		0.1	μA
Forward voltage	V <sub>F</sub>	I <sub>F</sub> =100mA		1.2	V
Diode capacitance	C <sub>D</sub>	V <sub>R</sub> =0, f=1MHz		3.5	pF
Reverse recovery time	t <sub>rr</sub>	V <sub>R</sub> =6V, I <sub>F</sub> =I <sub>R</sub> =5mA		4	ns

### Typical Characteristics

